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Amendments to the Specification:

Please replace paragraph [0003] with the following rewritten paragraph.

[0003] Compared with a CRT (cathode ray tube) display, the LCD has the advantages of less weight, smaller volume, and lower radiation. Hence, we can expect that the LCD will substitute

the CRT display to be the most as a popular display in the future.

Please replace paragraph [0005] with the following rewritten paragraph.

[0005] A Black Matrix may be plated on a CF to increase-contract contrast and prevent-mix mixture of-color colors and leakage of light. Hence, the LCD is better than the CRT display in resolution. However, if the resolution is promoted enhanced without narrowing the pitch of the pixels-being narrowed, the aperture ratio of pixels will be reduced and the brightness of the LCD will decrease. Hence, narrowing of the Black Matrix or studying other-methods alternatives to

improve the brightness is an important issue.

Please replace paragraph [0009] with the following rewritten paragraph.

[0009] The other aspect of the present invention is to reduce the capacity capacitance effect

between a signal line and a pixel electrode.

Please replace paragraph [0010] with the following rewritten paragraph.

[0010] In the present invention, a first gate line and a second gate are formed on a substrate.

The first gate line intersects with and is insulated from and the second gate line are insulated

from each other and are non-parallel to each other. After that, an insulation layer, a

semiconductor layer, a data line, a passivation layer, a low dielectric constant layer and a pixel

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electrode are formed sequentially. The data line overlaps the first gate line. A dielectric constant layer is a low dielectric constant layer. The pixel electrode overlaps with a portion of the first gate line and a portion of the second gate line. The data line overlaps with a portion of the first gate line. The portion of the first gate line overlapped by the pixel electrode is different from the portion of the first gate line overlapped by the data line. Therefore, the eapacity capacitance effect between the pixel electrode and the data line is avoided. In the second embodiment of the present invention, another kind of LCD is disclosed. The first gate line is replaced by a gate line including a pair of gate lines that are parallel to each other and separated by a gap.

Please replace paragraph [0019] with the following rewritten paragraph.

[0019] Fig. 1a is a schematic diagram of the first embodiment of the present invention. The LCD of the present invention includes a plurality of first gate lines 11, a plurality of second gate lines 12, a plurality of data lines 19 and a plurality of pixel electrodes 13. Only one of the pixels is illustrated in Fig. 1a. The first gate line 11-intersects with and is insulated from and the second gate line 12 are insulated from each other and are non-parallel to each other. The data line 19 overlaps a portion of the first gate line 11. The pixel electrode 13 also overlaps a portion of the first gate line 11 and a portion of the second gate line 12. However, in the first gate line_11, the overlapping portion of the data line 19 is different from the-one overlapping portion of the pixel electrode 13.

Please replace paragraph [0020] with the following rewritten paragraph.

[0020] Fig. 1b is a cross-sectional diagram along the line I-I' of Fig. 1a. On a substrate, such as a glass substrate, the first gate line 11, an insulation layer 15, a semiconductor layer 17, a data line 19, a passivation layer 21, a low dielectric constant layer 23 and a pixel electrode 13 are formed sequentially. Obviously, the portion that the data line 19-overlaps overlapping the first

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gate line 11 is different from the portion-that of the pixel electrode 13-overlaps overlapping the first gate line 11.

Please replace paragraph [0022] with the following rewritten paragraph.

[0022] In the present invention, the material of the insulation layer 15 includes-a an Si₃N₄ layer depositing above the first gate line 11, the second gate line 12 and the substrate 100. The material of the semiconductor layer 17 includes an undoped Si amorphous layer and a doped Si amorphous layer. The material of passivation layer 21 includes Si₃N₄. The low dielectric constant layer 23 is a transparent material with low dielectric constant, such as the acrylic. The material of the pixel electrode 13 includes ITO (Indium Tin Oxide).

Please replace paragraph [0023] with the following rewritten paragraph.

[0023] Fig. 2a is a schematic diagram of the second embodiment of the present invention. In the present invention, an LCD includes a plurality of gate line pairs 31, a plurality of gate lines 32, a plurality of data lines 39 and a plurality of pixel electrodes 33. Only one pixel is illustrated in Fig. 2a. The gate line pair 31-intersects with and is insulated from and the gate line pair 32 are insulated from each other and are non-parallel to each other. The gate line pair 31 includes a first gate line 311 and a second gate line 312. The first gate line 311 parallels the second gate line 312 with a gap 314 therebetween. The data line 39 overlaps a portion of the gate line pair 31 and the gap 314. Besides, the pixel electrode 33 also overlaps a portion of the gate line pair pair 31. However, in the gate-lines line pair 31, the overlapping portion of the data line 39 is different from the same overlapping portion of the pixel electrode 33. Likewise, the pixel electrode 33 also overlaps a portion of the gate line 32.

Please replace paragraph [0025] with the following rewritten paragraph.

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[0025] Fig. 2b is a cross-sectional diagram along the line III-III' of Fig. 2a. On a substrate, such as a glass substrate, the first-gate line pair 31, an insulation layer 35, a semiconductor layer 37, a data line 39, a passivation layer 41, a low dielectric constant layer 43 and a pixel electrode 33 are formed sequentially. Obviously, the portion that the data line 39 overlaps the first gate line pair 31 is different from the portion that of the pixel electrode 33 overlaps overlapping the first-gate line pair 31.

Please replace paragraph [0027] with the following rewritten paragraph.

[0027] In the present invention, the material of the insulation layer 35 includes—a <u>an Si₃N₄</u> layer depositing above the—data gate line pair 31, the gate line 32 and the substrate 300. The material of the semiconductor layer 37 includes an undoped Si amorphous layer and a doped Si amorphous layer. The material of passivation layer 41 includes Si₃N₄. The low dielectric constant layer 43 is a transparent material with low dielectric constant, such as the acrylic. The material of the pixel electrode 33 includes ITO (Indium Tin Oxide).

Please replace paragraph [0028] with the following rewritten paragraph.

[0028] The structure of an LCD proposed in the present invention may effectively increase the aperture ratio and avoid the leakage of light. Moreover, it may reduce the disconnection caused by a signal line to reduce the eapacity capacitance effect between a signal line and a pixel electrode.

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Please replace "Abstract" with the following rewritten paragraph.

Abstract The present invention provides a liquid crystal display including a substrate, a first gate line, a second gate line, an insulation layer, a data line, a passivation layer, a low dielectric constant layer, and a pixel electrode. The first gate line intersects with and is insulated from the second gate line. The pixel electrode overlaps a portion of the first gate line and a portion of the second gate line. The data line overlaps a portion of the first gate line. The portion of the first gate line overlapped by the pixel electrode is different from the portion of the first gate line overlapped by the data line. Therefore, the eapacity capacitance effect between the pixel electrode and the data line is reduced.